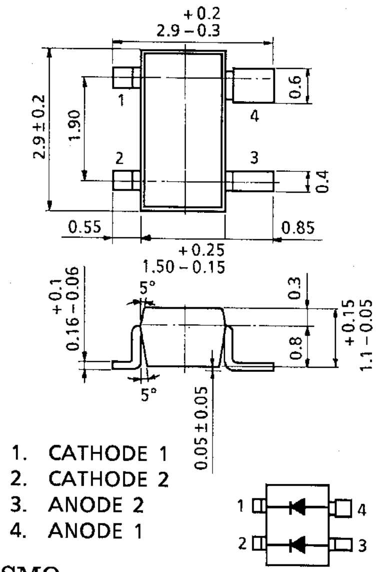
TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

1SS391

Low Voltage High Speed Switching

- Low forward voltage : $V_{F\ (2)} = 0.23V$ (typ.) @$I_F = 5mA$
- Small package : SC-61

Unit: mm



1. CATHODE 1
2. CATHODE 2
3. ANODE 2
4. ANODE 1

SMQ

JEDEC	—
EIAJ	SC-61
TOSHIBA	2-3J1A

Weight: 0.013g

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse Voltage	V_{RM}	15	V
Reverse voltage	V_R	10	V
Maximum (peak) forward current	I_{FM}	200 *	mA
Average forward current	I_O	100 *	mA
Surge current (10ms)	I_{FSM}	1 *	A
Power dissipation	P	150	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C
Operating temperature range	T_{opr}	−40~100	°C

*: Unit rating. Total rating = unit rating × 1.5

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_{F\ (1)}$	—	$I_F = 1mA$	—	0.18	—	V
	$V_{F\ (2)}$	—	$I_F = 5mA$	—	0.23	0.30	V
	$V_{F\ (3)}$	—	$I_F = 100mA$	—	0.35	0.50	V
Reverse current	I_R	—	$V_R = 10V$	—	—	20	μA
Total capacitance	C_T	—	$V_R = 0$, f = 1MHz	—	20	40	pF

Marking